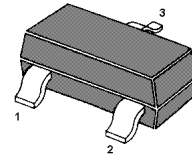


# MMBTSC6571

## NPN Silicon Epitaxial Planar Transistor

for general amplifier applications.



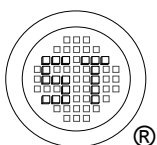
1. Base 2. Emitter 3. Collector  
TO-236 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	60	V
Collector Emitter Voltage	$V_{CEO}$	50	V
Emitter Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	100	mA
Peak Collector Current	$I_{CP}$	200	mA
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$ , $I_C = 2\text{ mA}$ Current Gain Group Q R S at $V_{CE} = 2\text{ V}$ , $I_C = 100\text{ mA}$	$h_{FE}$	160	-	260	-
	$h_{FE}$	210	-	340	-
	$h_{FE}$	290	-	460	-
	$h_{FE}$	90	-	-	-
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	$I_{CBO}$	-	-	10	nA
Collector Emitter Cutoff Current at $V_{CE} = 50\text{ V}$	$I_{CEO}$	-	-	100	$\mu\text{A}$
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	$I_{EBO}$	-	-	10	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	7	-	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Transition frequency at $V_{CB} = 10\text{ V}$ , $-I_E = 2\text{ mA}$ , $f = 200\text{ MHz}$	$f_T$	-	150	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	3.5	-	pF

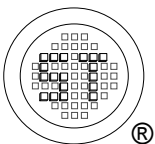
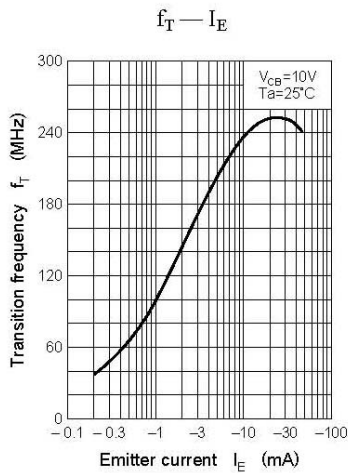
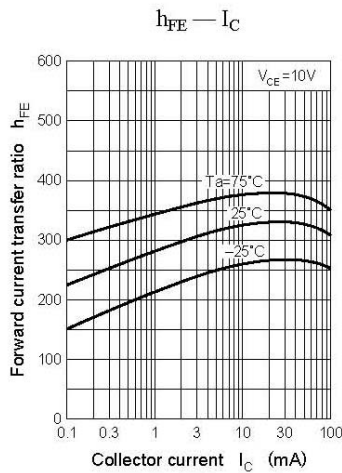
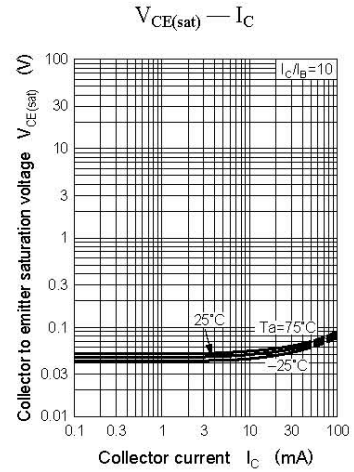
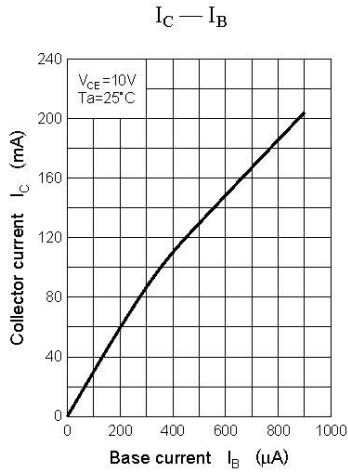
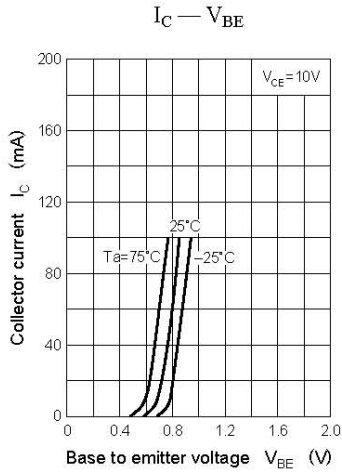
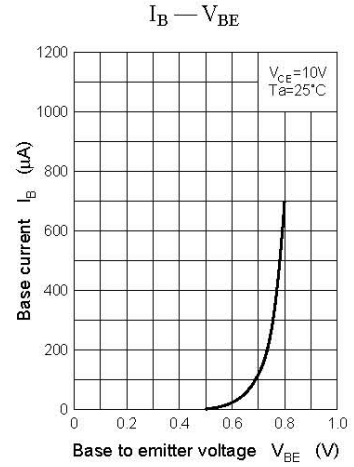
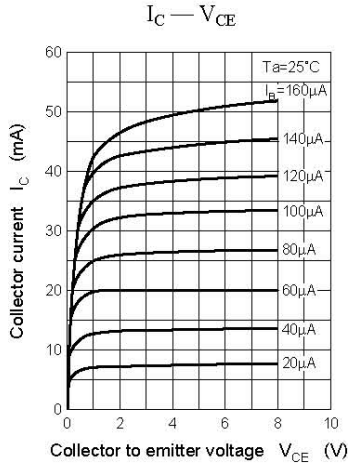
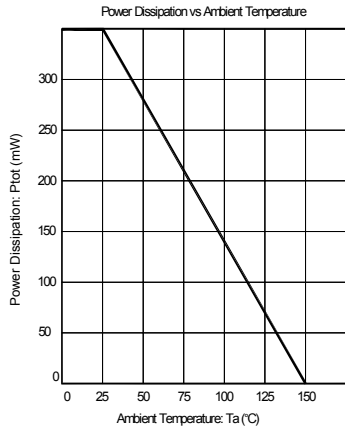


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Dated: 16/03/2015 Rev: 02

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